

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE40P25G uses advanced trench technology to provide excellent $R_{DS(ON)}$. This device is suitable for use as a load switch or power management.

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!
100% ΔV_{ds} TESTED!

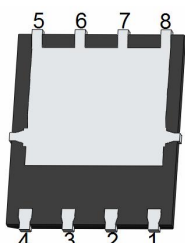
General Features

- $V_{DS} = -40V, I_D = -25A$
 $R_{DS(ON)} = 11.5m\Omega$ (typical) @ $V_{GS} = 10V$
 $R_{DS(ON)} = 18.5m\Omega$ (typical) @ $V_{GS} = 4.5V$
- High density cell design for ultra low R_{dson}
- Very low on-resistance $R_{DS(on)}$
- Good stability and uniformity with high E_{AS}
- 150 °C operating temperature
- Pb-free lead plating

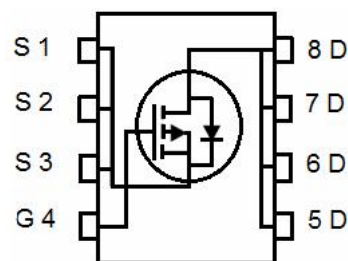
DFN 5X6



Top View



Bottom View



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE40P25G	NCE40P25G	DFN 5x6-8L	-	-	-

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-25	A
Drain Current-Pulsed (Note 1)	I_{DM}	-100	A
Maximum Power Dissipation	P_D	35	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta JC}$	3.6	$^\circ C/W$
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-40V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1.2	-1.8	-2.4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-20A	-	11.5	14	mΩ
	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-20A	-	18.5	23	
Forward Transconductance	g _{FS}	V _{DS} =-10V, I _D =-20A	-	25	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =-20V, V _{GS} =0V, F=1.0MHz	-	2960	-	PF
Output Capacitance	C _{oss}		-	370	-	PF
Reverse Transfer Capacitance	C _{rss}		-	310	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-20V, I _D =-20A, V _{GS} =-10V, R _{GEN} =3Ω	-	10	-	nS
Turn-on Rise Time	t _r		-	18	-	nS
Turn-Off Delay Time	t _{d(off)}		-	38	-	nS
Turn-Off Fall Time	t _f		-	24	-	nS
Total Gate Charge	Q _g	V _{DS} =-20V, I _D =-20A, V _{GS} =-10V	-	42.2	-	nC
Gate-Source Charge	Q _{gs}		-	6.9	-	nC
Gate-Drain Charge	Q _{gd}		-	9.7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-20A	-	-	-1.2	V

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

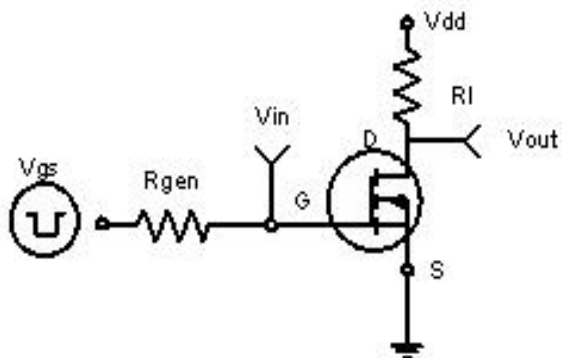


Figure 1 Switching Test Circuit

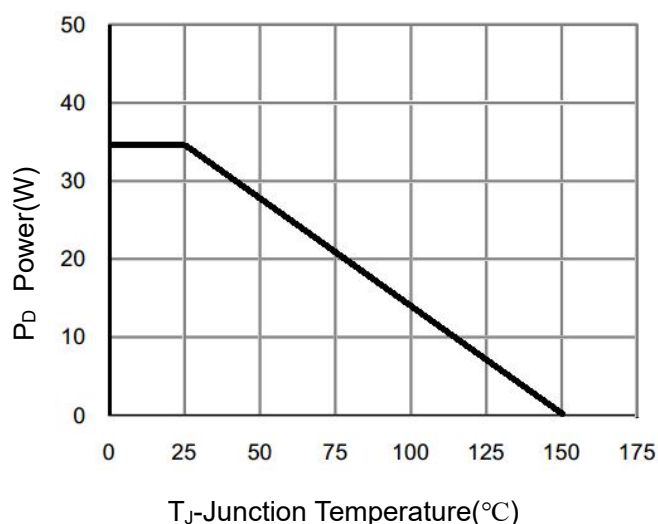


Figure 3 Power Dissipation

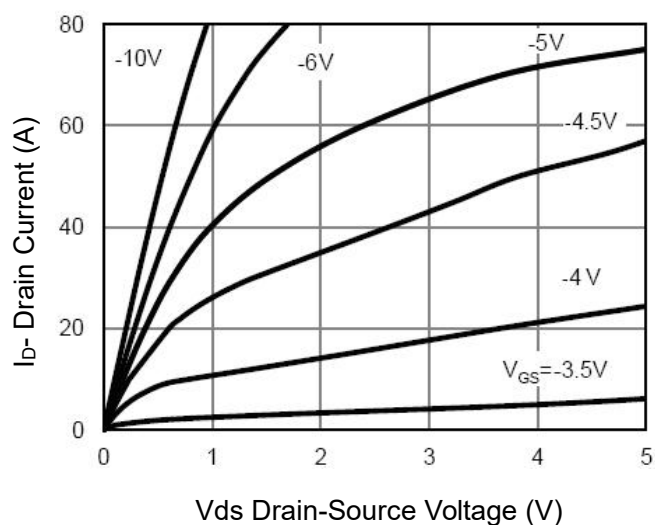


Figure 5 Output Characteristics

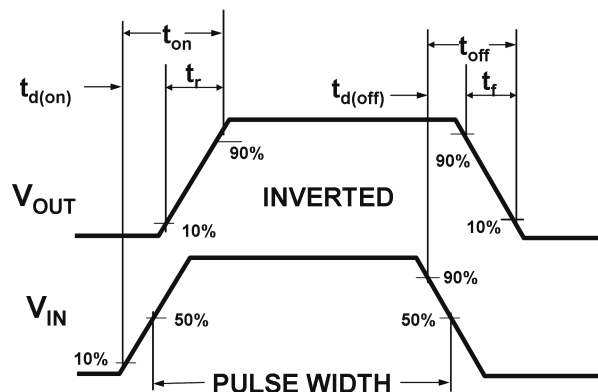


Figure 2 Switching Waveforms

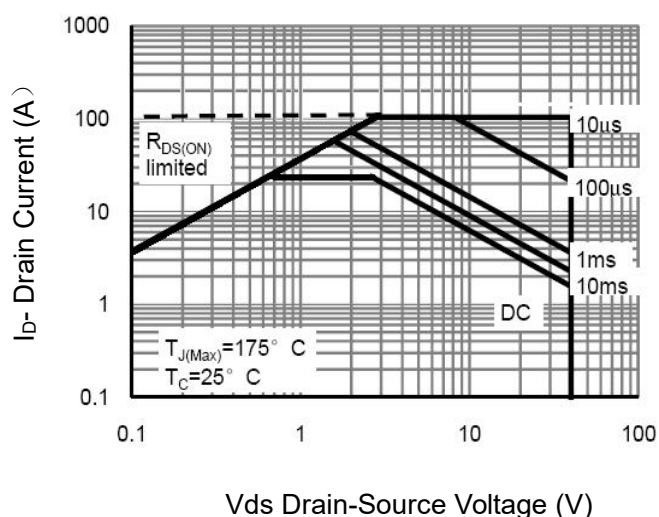


Figure 4 Safe Operation Area

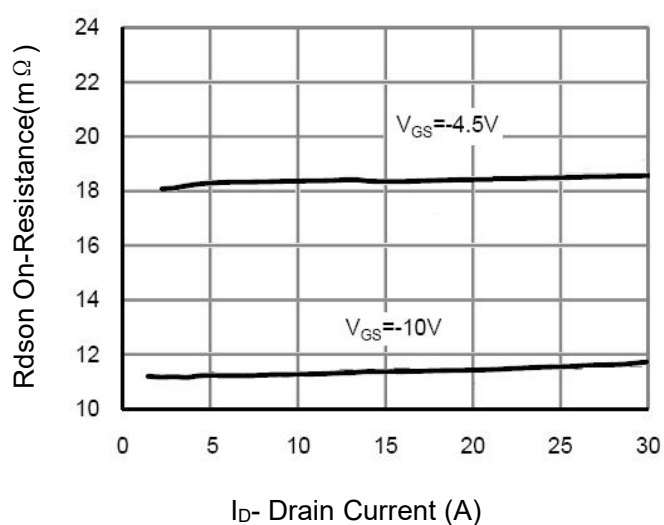


Figure 6 Drain-Source On-Resistance

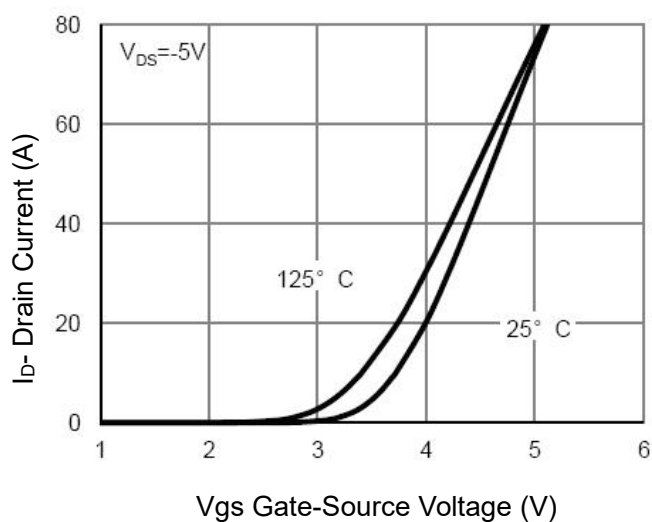


Figure 7 Transfer Characteristics

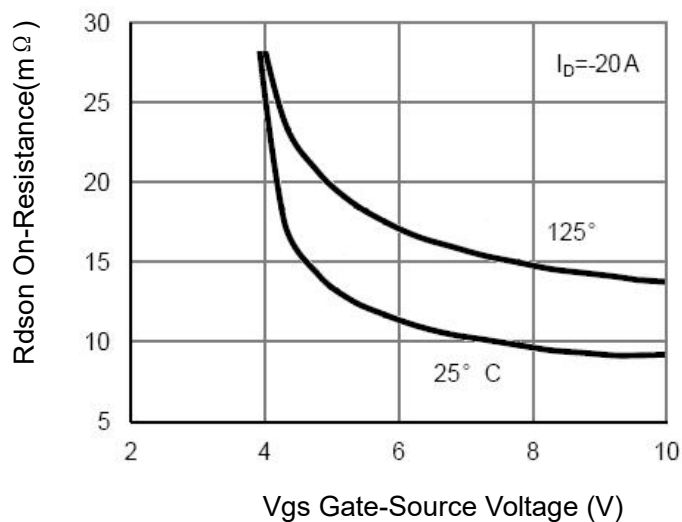


Figure 9 Rdson vs Vgs

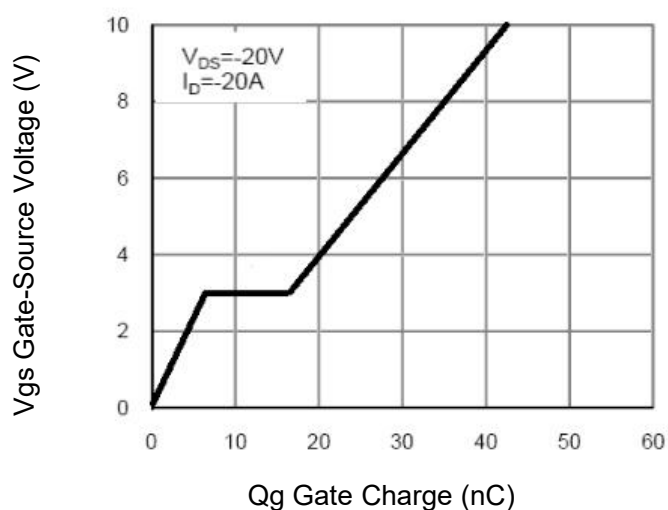


Figure 11 Gate Charge

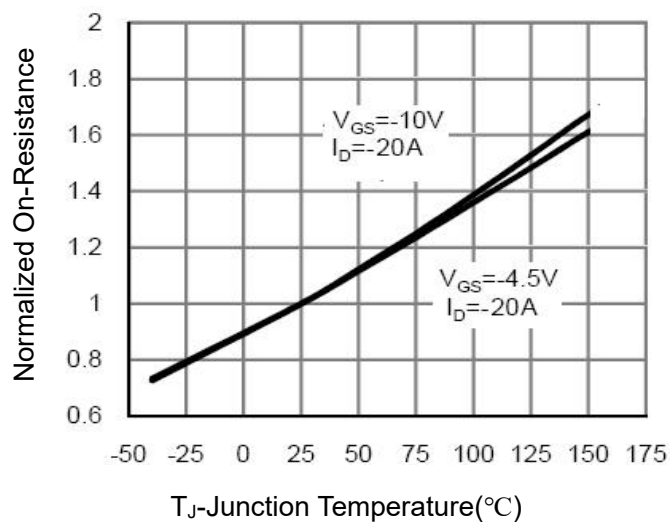


Figure 8 Drain-Source On-Resistance

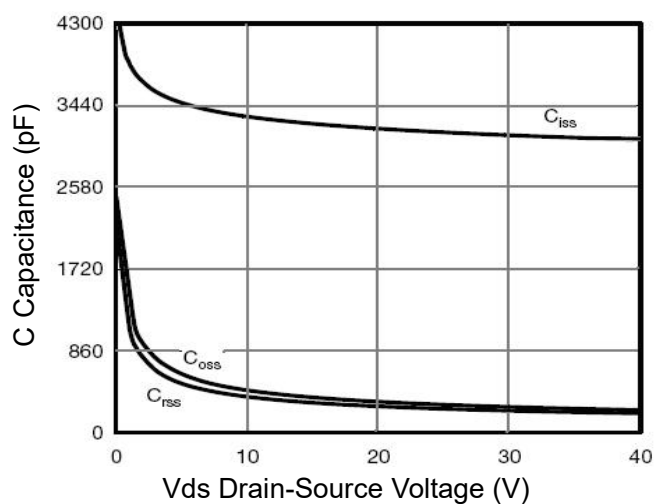


Figure 10 Capacitance vs Vds

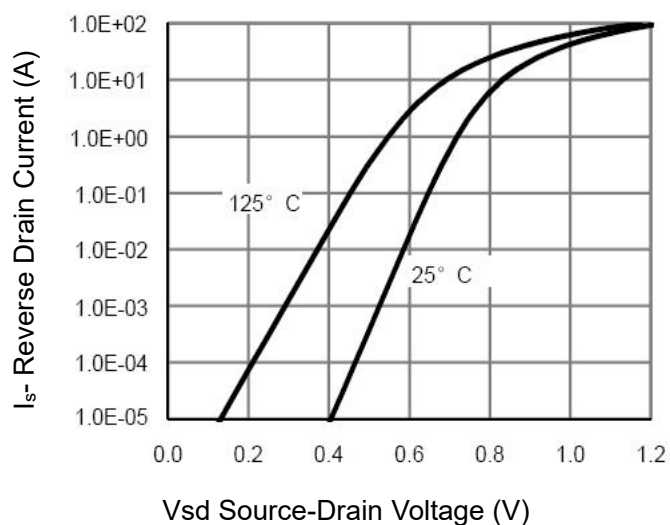


Figure 12 Source- Drain Diode Forward

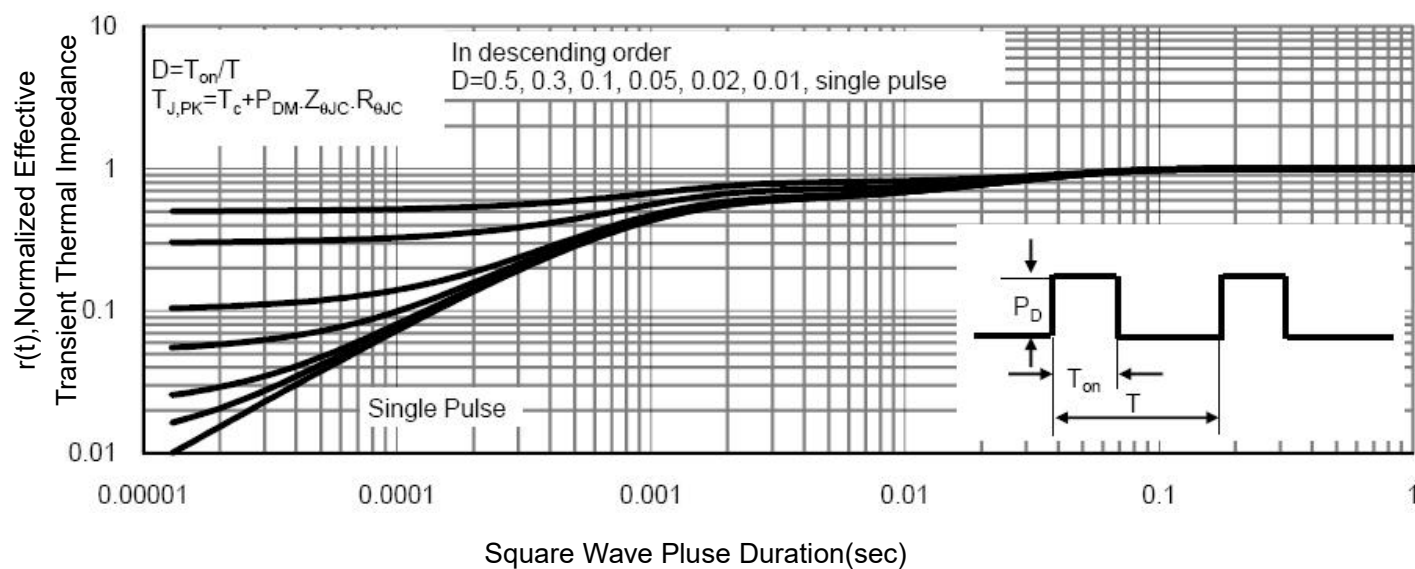
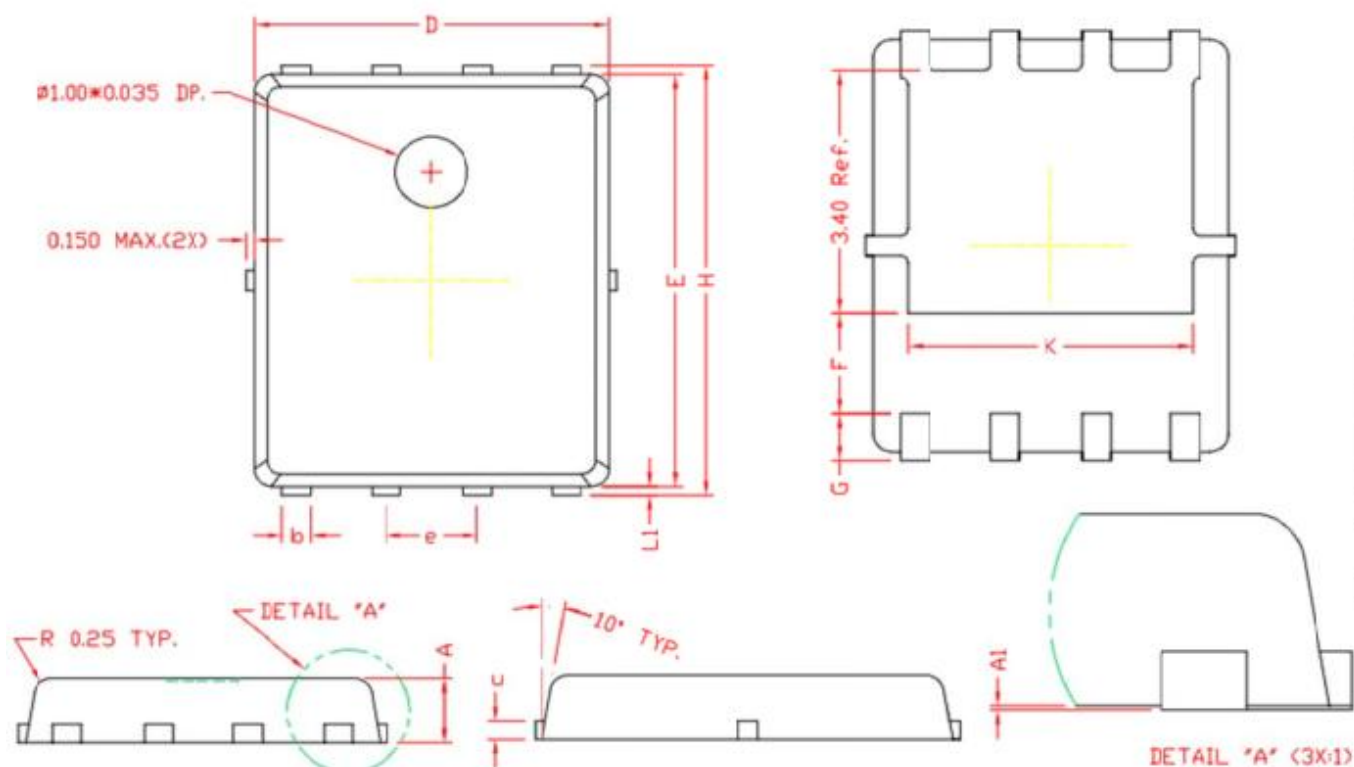


Figure 13 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.80	0.90	1.00
A1	0.00	0.03	0.05
b	0.35	0.42	0.49
c	0.254 REF.		
D	4.90	5.00	5.10
F	1.40 REF.		
E	5.70	5.80	5.90
e	1.27 BSC.		
H	5.95	6.08	6.20
L1	0.10	0.14	0.18
G	0.60 REF.		
K	4.00 REF.		

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